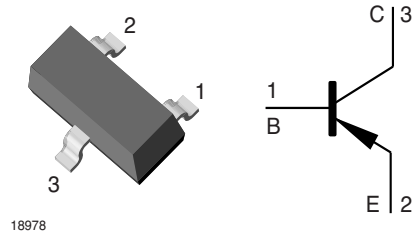


Small Signal Transistors (PNP)

Features

- PNP Silicon Epitaxial Planar Transistors
- Suited for low level, low noise, low frequency applications in hybrid circuits.
- Low Current, Low Voltage.
- As complementary types, BCW60 Series NPN transistors are recommended.



Mechanical Data

Case: SOT-23 Plastic case

Weight: approx. 8.8 mg

Marking:

BCW61A = BA
 BCW61B = BB
 BCW61C = BC
 BCW61D = BD

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box
 GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

Pinning:

1 = Base, 2 = Emitter, 3 = Collector

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Collector-emitter voltage		- V_{CEO}	32	V
Collector-base voltage		- V_{CBO}	32	V
Emitter-base voltage		- V_{EBO}	5.0	V
Collector current (DC)		- I_C	100	mA
Peak collector current		- I_{CM}	200	mA
Base current (DC)		- I_B	50	mA
Power dissipation	$T_A = 25\text{ }^{\circ}\text{C}$	P_{tot}	250	mW

Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit
Maximum junction temperature		T_J	150	$^{\circ}\text{C}$
Storage temperature range		T_S	- 65 to + 150	$^{\circ}\text{C}$
Thermal resistance junction to ambient air		$R_{\theta JA}$	500 ¹⁾	$^{\circ}\text{C/W}$

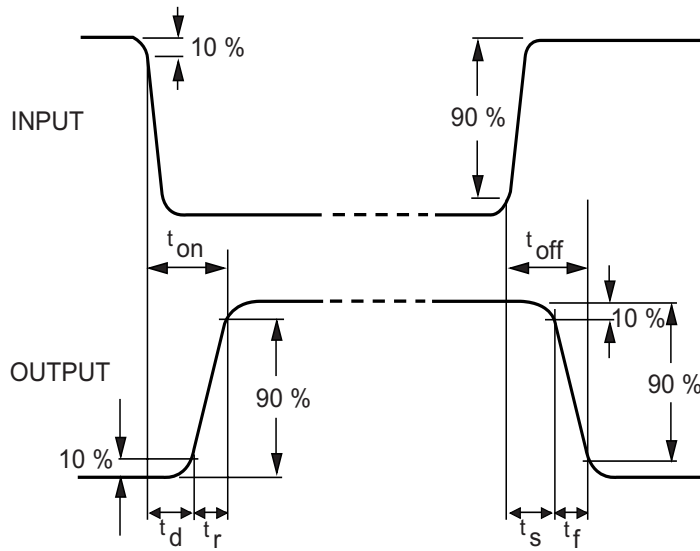
¹⁾ Mounted on an FR-4 printed-circuit board.

Electrical DC Characteristics

Parameter	Test condition	Part	Symbol	Min	Typ	Max	Unit
DC current gain	- $V_{CE} = 5\text{ V}$, - $I_C = 10\ \mu\text{A}$	BCW61A	h_{FE}				
		BCW61B	h_{FE}	30			
		BCW61C	h_{FE}	40			
		BCW61D	h_{FE}	100			
	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$	BCW61A	h_{FE}	120		220	
		BCW61B	h_{FE}	180		310	
		BCW61C	h_{FE}	250		460	
		BCW61D	h_{FE}	380		630	
	- $V_{CE} = 1\text{ V}$, - $I_C = 50\text{ mA}$	BCW61B	h_{FE}	60			
		BCW61B	h_{FE}	80			
		BCW61C	h_{FE}	100			
		BCW61D	h_{FE}	110			
Collector - emitter saturation voltage	- $I_C = 10\text{ mA}$, - $I_B = 0.25\text{ mA}$		V_{CEsat}	60		250	mV
	- $I_C = 50\text{ mA}$, - $I_B = 1.25\text{ mA}$		V_{CEsat}	120		550	mV
Base - emitter saturation voltage	- $I_C = 10\text{ mA}$, - $I_B = 0.25\text{ mA}$		V_{BEsat}	600		850	mV
	- $I_C = 50\text{ mA}$, - $I_B = 1.25\text{ mA}$		V_{BEsat}	680		1050	mV
Base - emitter voltage	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$		V_{BE}	600	650	750	mV
	- $V_{CE} = 5\text{ V}$, - $I_C = 10\ \mu\text{A}$		V_{BE}		520		mV
	- $V_{CE} = 1\text{ V}$, - $I_C = 50\text{ mA}$		V_{BE}		780		mV
Collector-emitter cut-off current	- $V_{CE} = 32\text{ V}$, $V_{EB} = 0\text{ V}$		I_{CES}			20	nA
	- $V_{CE} = 32\text{ V}$, $V_{EB} = 0\text{ V}$, $T_A = 150\text{ }^\circ\text{C}$		I_{CES}			20	μA
Emitter-base cut-off current	- $V_{EB} = 4\text{ V}$, $I_C = 0$		I_{EBO}			20	nA

Electrical AC Characteristics

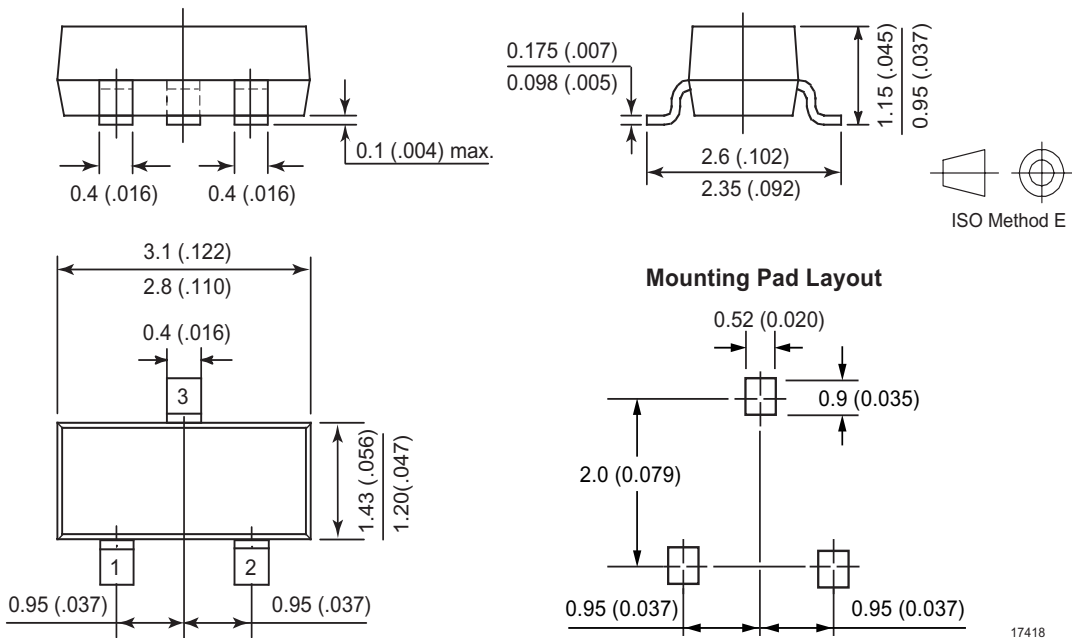
Parameter	Test condition	Part	Symbol	Min	Typ	Max	Unit
Gain - bandwidth product	- $V_{CE} = 5\text{ V}$, - $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$		f_T	100			MHz
Collector - base capacitance	- $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$, $I_E = 0$		C_{CBO}		4.5		pF
Emitter - base capacitance	- $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $I_C = 0$		C_{EBO}		11		pF
Noise figure	- $V_{CE} = 5\text{ V}$, - $I_C = 200\ \mu\text{A}$, $R_S = 2\text{ k}\Omega$, $f = 1\text{ kHz}$, $B = 200\text{ Hz}$		F		2	6	dB
Small signal current gain	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1.0\text{ kHz}$	BCW61A	h_{fe}		200		
		BCW61B	h_{fe}		260		
		BCW61C	h_{fe}		330		
		BCW61D	h_{fe}		520		
Turn - on time	$R_L = 990\ \Omega$ (see fig.1) - $V_{CC} = 10\text{ V}$, - $I_C = 10\text{ mA}$, - $I_{B(on)} = I_{B(off)} = 1\text{ mA}$		t_{on}		85	150	ns
Turn - off time	$R_L = 990\ \Omega$ (see fig.1) - $V_{CC} = 10\text{ V}$, - $I_C = 10\text{ mA}$, - $I_{B(on)} = I_{B(off)} = 1\text{ mA}$		t_{off}		480	800	ns



19204

Figure 1. Switching Waveform

Package Dimensions in mm (Inches)



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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